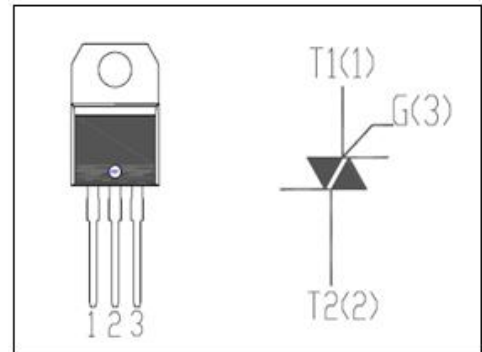


isc Triacs

BTB04-600

FEATURES

- With TO-220AB non insulated package
- Suitable for general purpose applications where gate high sensitivity is required. Application on 4Q such as phase control and static switching.



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	MIN	UNIT
V <sub>DRM</sub>	Repetitive peak off-state voltage	600	V
V <sub>RRM</sub>	Repetitive peak off-state voltage	600	V
I <sub>T(RMS)</sub>	RMS on-state current (full sine wave)T <sub>j</sub> =95°C	4	A
I <sub>TSM</sub>	Non-repetitive peak on-state current t <sub>p</sub> =10ms	40	A
T <sub>j</sub>	Operating junction temperature	110	°C
T <sub>stg</sub>	Storage temperature	-40~150	°C
R <sub>th(j-c)</sub>	Thermal resistance, junction to case	2.4	°C/W
R <sub>th(j-a)</sub>	Thermal resistance, junction to ambient	60	°C/W

ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT	
I <sub>RRM</sub>	Repetitive peak reverse current	V <sub>R</sub> =V <sub>RRM</sub> , V <sub>R</sub> =V <sub>RRM</sub> , T <sub>j</sub> =110°C	0.01 0.75	mA	
I <sub>DRM</sub>	Repetitive peak off-state current	V <sub>D</sub> =V <sub>DRM</sub> , V <sub>D</sub> =V <sub>DRM</sub> , T <sub>j</sub> =110°C	0.01 0.75	mA	
I <sub>GT</sub>	Gate trigger current	V <sub>D</sub> =12V; R <sub>L</sub> = 30 Ω	I	10	mA
			II	10	
			III	10	
			IV	25	
I <sub>H</sub>	Holding current	I <sub>GT</sub> = 0.1A, Gate Open	25	mA	
V <sub>GT</sub>	Gate trigger voltage all quadrant	V <sub>D</sub> =12V; R <sub>L</sub> = 30 Ω	1.5	V	
V <sub>TM</sub>	On-state voltage	I <sub>T</sub> = 5.5A ; t <sub>p</sub> = 380 μ s	1.65	V	